

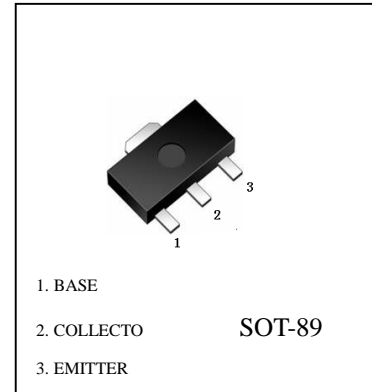
FEATURES

- High breakdown voltage and high current. $BV_{CEO}=-80V, I_C=-1A$
- Good h_{FE} Linearity.
- Low $V_{CE(sat)}$.
- Complements the 2SD1898.

Marking: ZL

Maximum Ratings ($T_a=25\text{ }^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-80	V
Collector-Emitter Voltage	V_{CEO}	-80	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current -Continuous	I_C	1	A
Collector Power dissipation	P_C	500	mW
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	-55to +150	$^{\circ}\text{C}$

2SB1260(PNP)


ELECTRICAL CHARACTERISTICS (@ $T_a=25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CBO}	$I_C=-50\mu\text{A}$ $I_E=0$	-80			V
Collector-emitter breakdown voltage	V_{CEO}	$I_C=-1\text{mA}$ $I_B=0$	-80			V
Emitter-base breakdown voltage	V_{EBO}	$I_E=-50\mu\text{A}$ $I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-60\text{V}$ $I_E=0$			-1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-4\text{V}, I_C=0$			-1	μA
DC current gain	h_{FE}	$V_{CE}=-3\text{V}$ $I_C=-100\mu\text{A}$	82		390	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-500\text{mA}$ $I_B=-50\text{mA}$			-0.4	V
Transition frequency	f_T	$V_{CE}=-5\text{V}, I_C=-50\text{mA},$ $f=30\text{MHz}$		100		MHz
Output Capacitance	C_{obo}	$V_{CB}=-10\text{V}$ $f=1.0\text{MHz}$ $I_E=0$	-	25		pF

2SB1260 Typical Characteristics

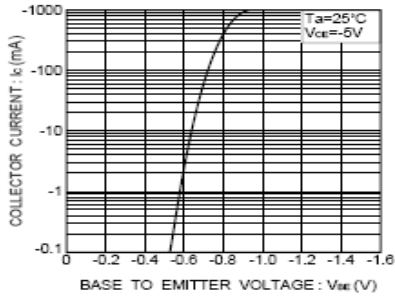


Fig.1 Grounded emitter propagation characteristics

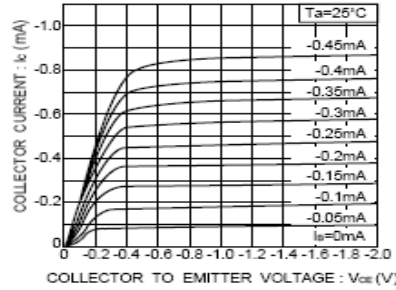


Fig.2 Grounded emitter output characteristics

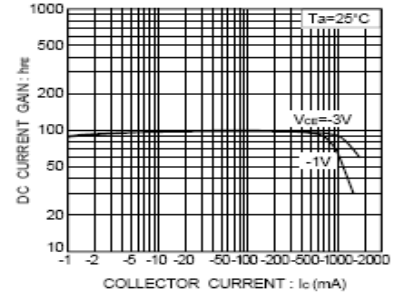


Fig.3 DC current gain vs. collector current

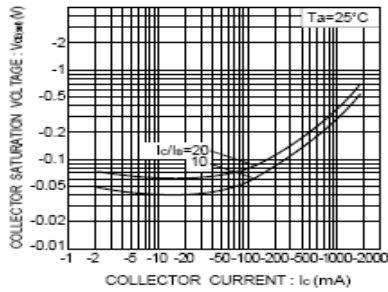


Fig.4 Collector-emitter saturation voltage vs. collector current

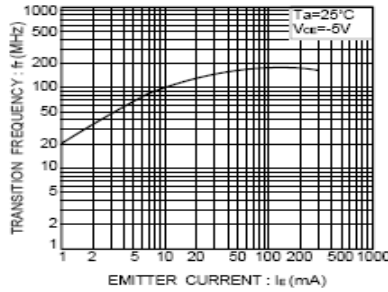


Fig.5 Gain bandwidth product vs. emitter current

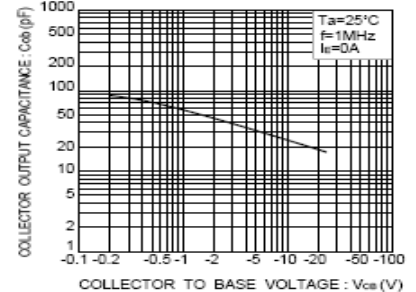


Fig.6 Collector output capacitance vs. collector-base voltage